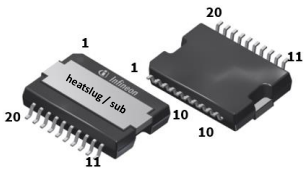
CoolGaN™ BDS 650 V G5

PG-DSO-20

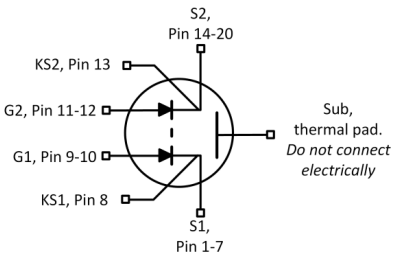
CoolGaN™ Bidirectional switch, enhancement-mode



Infineon's CoolGaN™ BiDirectional Switch (BDS) is an innovative solution in gallium nitride (GaN) transistor technology. The CoolGaN™ BDS 650 V G5 enables efficient voltage blocking in both directions, making it a versatile option for a wide range of applications. The CoolGaN™ BDS monolithically integrates a substrate voltage control circuit, thanks to Infineon's proprietary technology: this reduces design complexity. IGOT65R025B3 is offered in Infineon's DSO, top-side cooling package specially designed to enable the highest power densities for power-demanding industrial applications.

Features

- 650 V CoolGaN™ technology with 850 V_{SS} surge immunity
- Superior rugged Gate Injection Transistor (GIT) structure
- Dual-gate for independent bidirectional functionality
- Superior performance of $R_{SS(on)}$ over operating frequency
- Reliable Thermal Cycling on-Board (TCoB) performance
- Optimized for soft switching operation
- ESD-HBM robustness acc. ANSI/ESDA/JEDEC std. JS-001: 2 kV



Benefits

- Effective replacement of back-to-back uni-directional products
- Improves system efficiency and power density
- Enables higher switching frequency
- System cost reduction
- Enables new single stage isolated topologies

Potential applications

- Cycloconverter in solar µ-inverter

Product validation

Qualified according to relevant JEDEC tests.

Please note: Preliminary Datasheet to change without further notice.

Please note: The substrate thermal pad is for thermal coupling only, it should be electrically isolated from any electrical node in the system via isolation material.

Table 1 Key performance parameters

Parameter	Value	Unit
$V_{SS,cont}$	340	V_{AC}
$R_{SS(on),typ}$	25	mΩ
$Q_{GxSx,switch}$	9.5	nC
$I_{SS,pulse}$	±183.1	A
Q_{oss} @ 400 V_{SS} (switch)	149	nC

GaN Hal Pb RoHS

Part number	Package	Marking	Related links
IGOT65R025B3	PG-DSO-20	65R025B3	see Appendix A

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1 Maximum ratings

at T_j = 25°C, unless otherwise specified. Continuous application of maximum ratings can deteriorate transistor lifetime. For further information, contact your local Infineon sales office.

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Source-to-source voltage, continuous	$V_{SS,cont}$	-	-	340	V_{AC}	V_{GS}=0 V
Source-to-source voltage, transient	$V_{SS,trans}$	-650	-	650	V	t_{TRANS}=5 ms; V_{GS}=0 V
Source-to-source voltage, surge	$V_{SS,surge}$	-850	-	850	V	t_{SURGE}=1 µs; V_{GS}=0 V
Source-to-source AC line frequency	f_{SS}	45	-	-	Hz	V_{SS}=305 V_{AC}; ±431 V_{pk}
RMS current, source-to-source	$I_{SS,RMS}$	-45	-	45	A	T_C=25°C;
		-24.8		24.8		T_C=125°C; T_j=$T_{j,max}$
Pulsed current, source-to-source	$I_{SS,pulse}$	-183.1	-	183.1	A	T_j=25°C; I_{GS}=68.0 mA
		-131.4		131.4		T_j=125°C; I_{GS}=68.0 mA
Gate current, steady state (single gate)	$I_{G,ss}$	-	-	68	mA	T_j=-40°C to T_j=150°C; see Table 8
Gate current, pulsed (single gate) [1]	$I_{G,pulse}$	-	-	6800	mA	T_j=-40°C to T_j=150°C; t_{PULSE}=50 ns, f=100 kHz; see Table 8
Gate source voltage, continuous [1]	V_{GS}	-10	-	-	V	T_j=-40°C to T_j=150°C; see Table 8
Gate source voltage, pulsed [1]	$V_{GxSx,pulse}$	-25	-	-	V	T_j=-40°C to T_j=150°C; t_{PULSE}=50 ns, f=100 kHz; open source
Power dissipation	P_{tot}	-	-	176.6	W	T_C=25°C
Operating junction temperature	T_j	-40	-	150	°C	-
Storage temperature	T_{stg}	-40	-	150	°C	Max shelf life depends on storage conditions
Source-to-source voltage slew-rate	dv/dt	-	-	100	V/ns	-

[1] We recommend using an advanced driving technique to optimize the device performance. Please see gate drive application note for more details.

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2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.71	°C/W	-
Reflow soldering temperature	T_{sold}	-	-	260	°C	reflow MSL3

preliminary

3 Electrical characteristics

at T_j=25°C, unless specified otherwise

Table 4 Gate characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate threshold voltage: switch mode (OFF) to diode mode	$V_{GxSx(th),diode}$	0.8	1.15	1.6	V	I_{SS}=6.8 mA; V_{GySy}=0 V; V_{SS}=10 V; T_j=25°C;
		-	0.95	-		I_{SS}=6.8 mA; V_{GySy}=0 V; V_{SS}=10 V; T_j=150°C; see Table 9
Gate threshold voltage: diode mode to switch mode (ON)	$V_{GxSx(th),switch}$	0.7	1.08	1.5	V	I_{SS}=6.8 mA; I_{GySy}=0.68 mA; V_{SS}=10 V; T_j=25°C;
		-	0.83	-		I_{SS}=6.8 mA; I_{GySy}=0.68 mA; V_{SS}=10 V; T_j=150°C; see Table 9
Gate-Source reverse clamping voltage	$V_{GS,clamp}$	-8	-	-	V	$I_{GS,ss}$=-3.4 mA
Gate charge: diode mode to switch mode (ON)	$Q_{GxSx,switch}$	-	9.5	-	nC	V_{GxSx}=0 to 3 V; I_{GySy}=68 mA; V_{SS}=400 V, I_{SS}=20 A
Gate resistance	$R_{GS,int}$	-	0.37	-	Ω	LCR impedance measurement; f=f_{res}

Table 5 On-state characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Source-to-source on-state resistance	$R_{SS(on)}$	-	25	30	mΩ	I_{GS}=68 mA; I_{SS}=20 A; T_j=25°C
			52.5	-		I_{GS}=68 mA; I_{SS}=20 A; T_j=150°C

Table 6 Dynamic characteristics - switch mode, see Table 10

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance: switch mode	$C_{iss,switch}$	-	848	-	pF	V_{GS}=0 V; V_{SS}=400 V; f=1 MHz
Output capacitance: switch mode	$C_{oss,switch}$		315			
Reverse Transfer capacitance: switch mode	$C_{rss,switch}$		4			
Effective output capacitance, energy related: switch mode [2)]	$C_{o(er),switch}$	-	344	-	pF	V_{GS}=0 V; V_{SS}=400 V
Effective output capacitance, time related: switch mode [3)]	$C_{o(tr),switch}$	-	373	-	pF	V_{GS}=0 V; V_{SS}=0 to 400 V; I_{SS}=const
Output charge: switch mode	$Q_{oss,switch}$	-	149	-	nC	V_{GS}=0 V; V_{SS}=400 V

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[2] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{SS} is rising from 0 to 400 V
[3] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{SS} is rising from 0 to 400 V

Table 7 Dynamic characteristics - diode mode, see Table 11

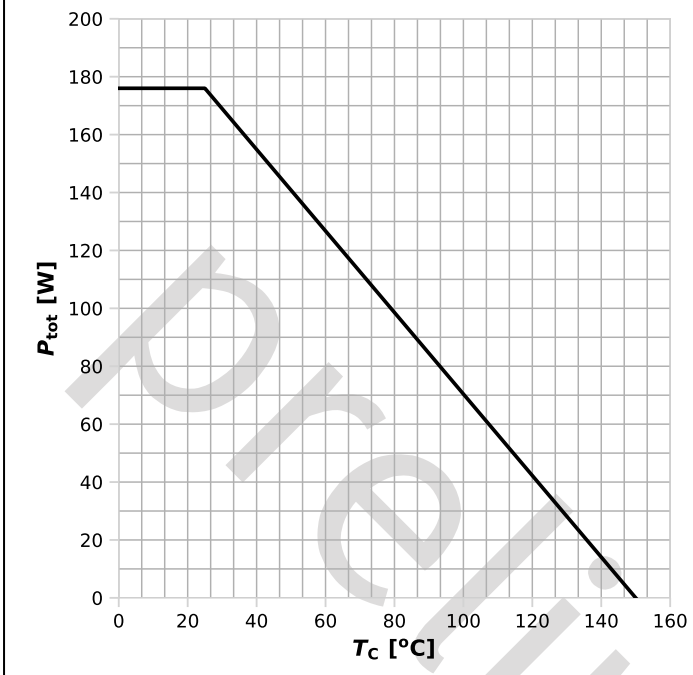
Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance: diode mode	$C_{iss,diode}$	-	856	-	pF	V_{GxSx}=0 V; I_{GySy}=0.68 mA; V_{SySx}=400 V; f=1 MHz
Output capacitance: diode mode	$C_{oss,diode}$		369			
Reverse Transfer capacitance: diode mode	$C_{rss,diode}$		5			
Effective output capacitance, energy related: diode mode [4]	$C_{o(er),diode}$	-	434	-	pF	V_{GxSx}=0 V; I_{GySy}=0.68 mA; V_{SySx}=400 V
Effective output capacitance, time related: diode mode [5]	$C_{o(tr),diode}$	-	498	-	pF	V_{GxSx}=0 V; I_{GySy}=0.68 mA; V_{SySx}=0 to 400 V; I_{SS}=const
Output charge: diode mode	$Q_{oss,diode}$	-	199	-	nC	V_{GxSx}=0 V; I_{GySy}=0.68 mA; V_{SySx}=400 V

[4] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{SS} is rising from 0 to 400 V
[5] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{SS} is rising from 0 to 400 V

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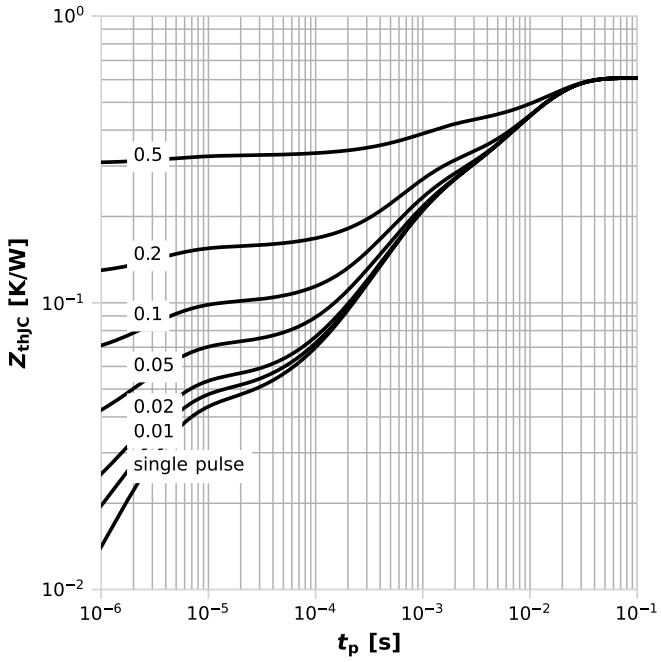
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



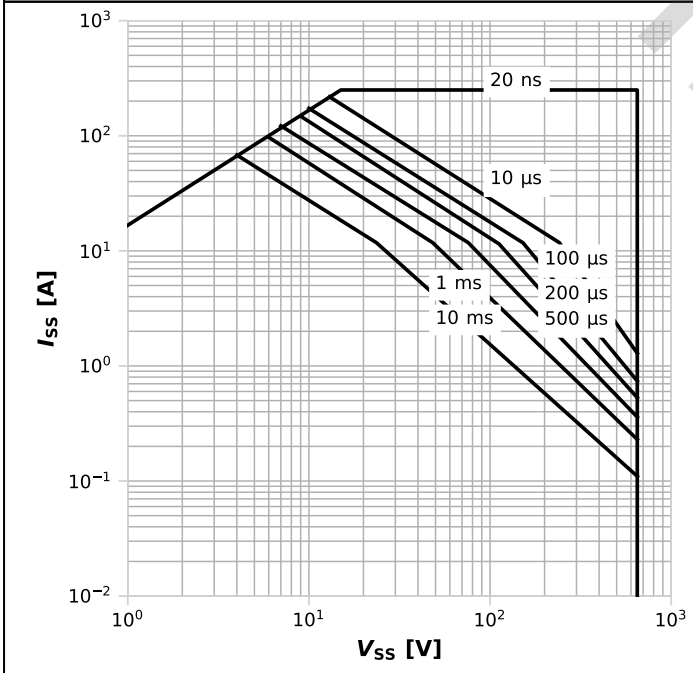
P_{tot}=f(T_C)

Diagram 2: Max. transient thermal impedance



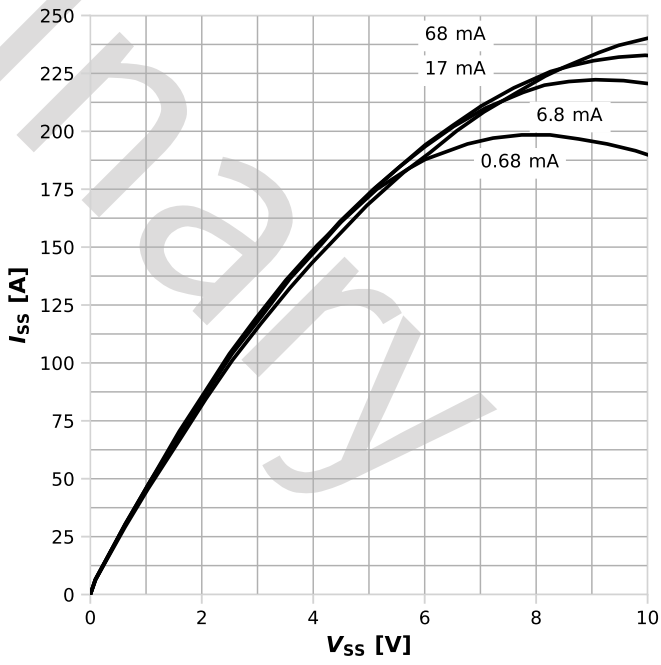
Z_{thJC} =f(t_P); parameter: D=t_p/T

Diagram 3: Safe operating area



I_D=f(V_{DS}); T_C=25°C; D=0; parameter: t_p

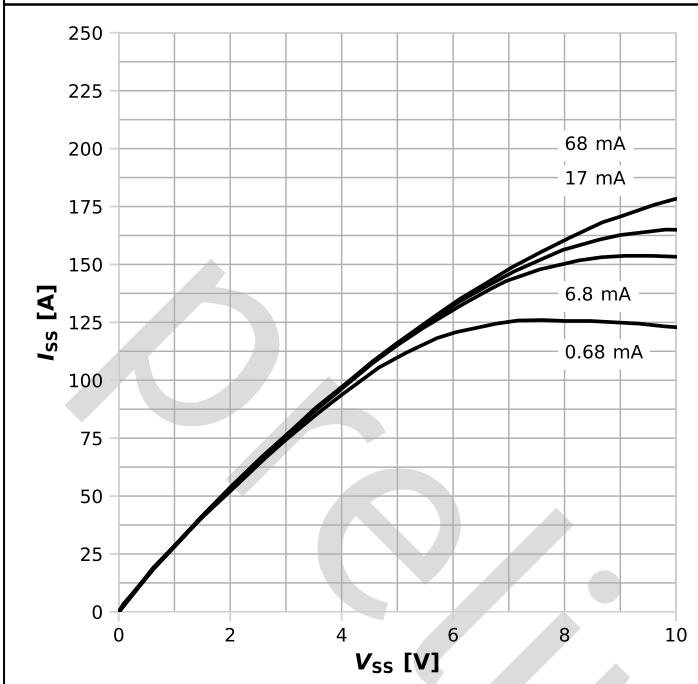
Diagram 4: Typ. output characteristics



I_{SS}=f(V_{SS}); I_{GySy}=68 mA; T_j=25°C; parameter: I_{GxSx}

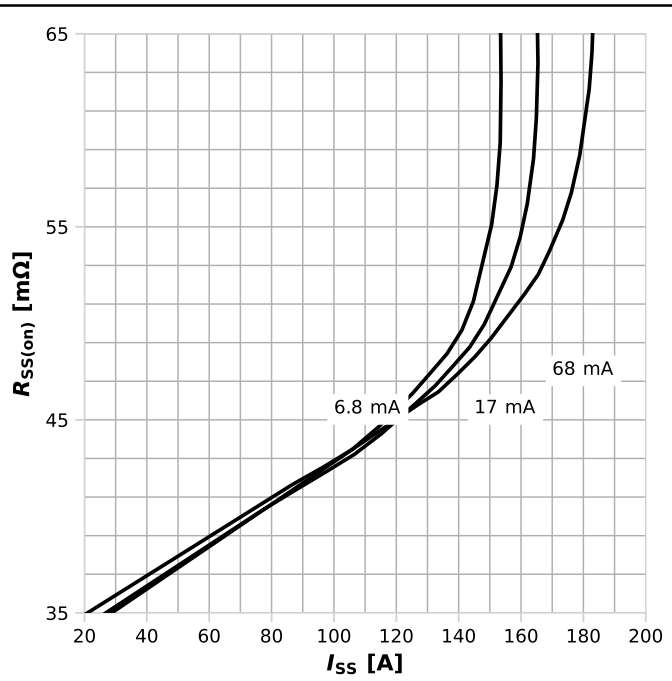
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Diagram 5: Typ. output characteristics



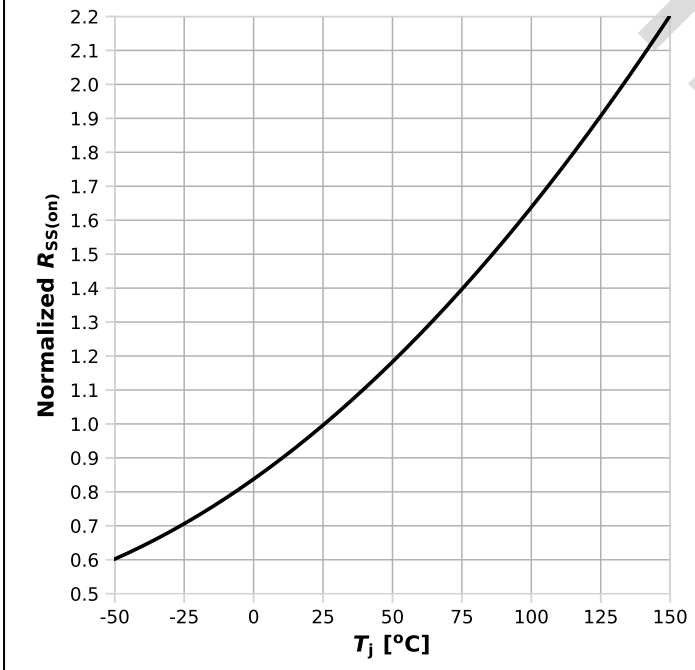
I_{SS}=f(V_{SS}); I_{GySy}=68 mA; T_j=125°C; parameter: I_{GxSx}

Diagram 6: Typ. source on-state resistance



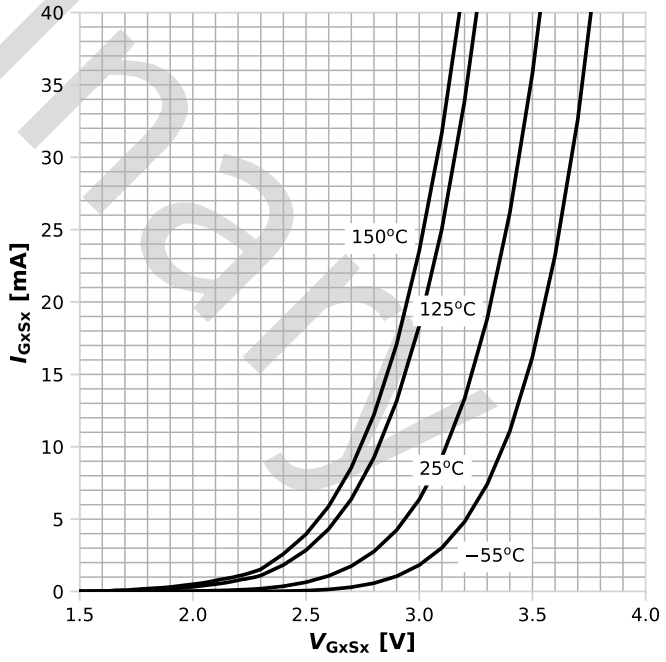
$R_{SS(on)}$=f(I_{SS}); I_{GySy}=68 mA; T_j=125°C; parameter: I_{GxSx}

Diagram 7: Typ. source-source on-state resistance



$R_{SS(on)}$=f(T_j); I_{GySy}=68 mA; I_{GxSx}=68 mA; I_{SS}=20 A; parameter: I_{GxSx}

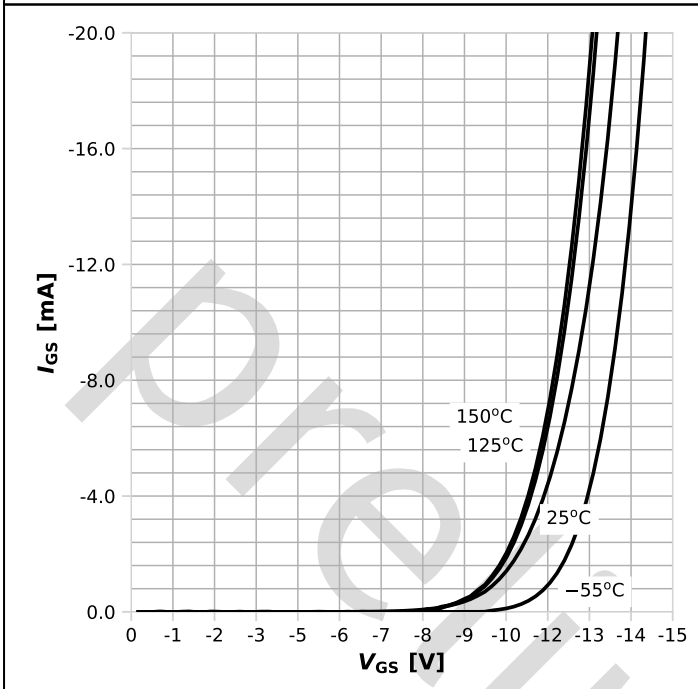
Diagram 8: Typ. gate characteristics forward



I_{GS}=f(V_{GxSx}); open S_y, G_y; parameter: T_j

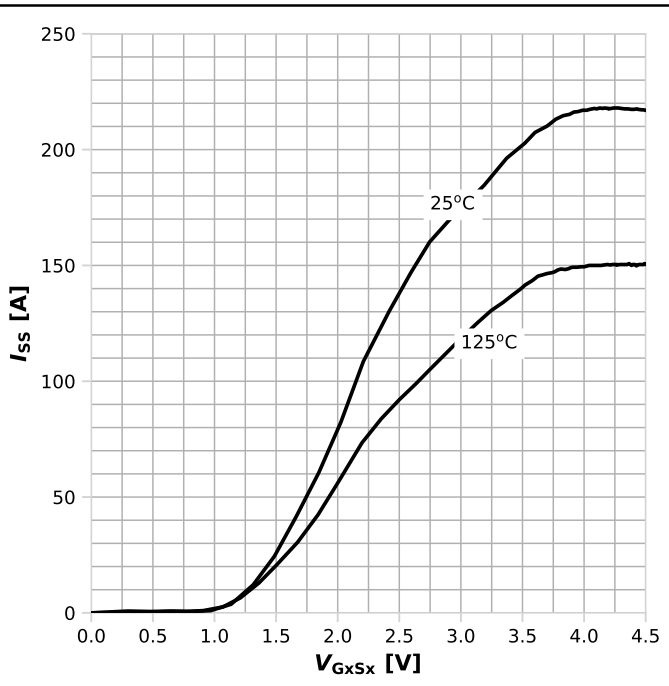
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Diagram 9: Typ. gate characteristics reverse



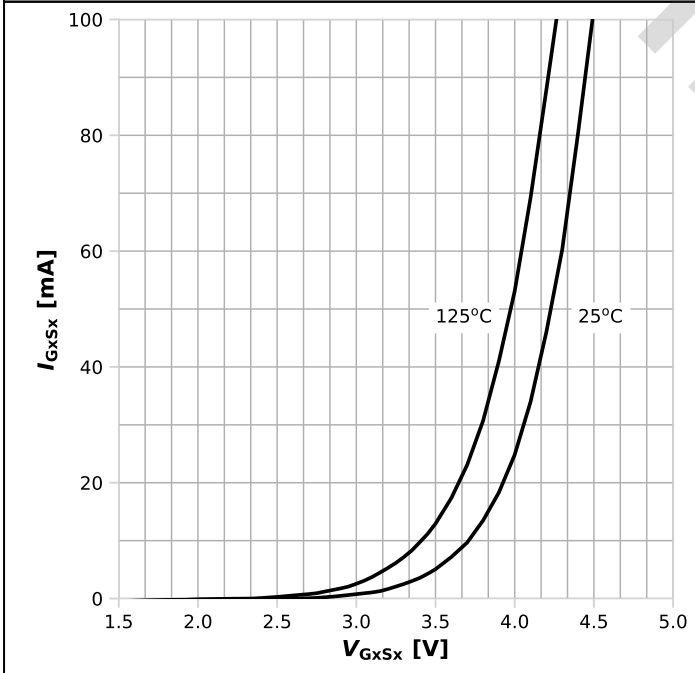
$I_{SG}=f(V_{SG})$; parameter: T_j

Diagram 10: Typ. transfer characteristics



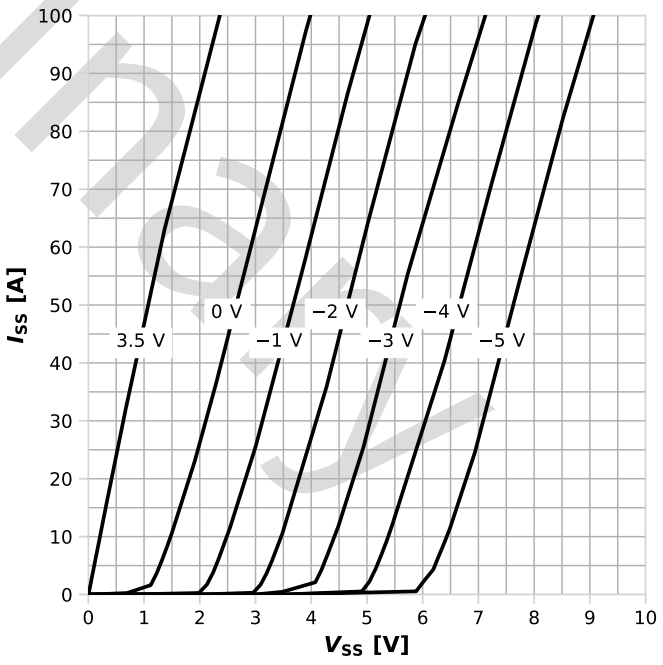
$I_{SS}=f(V_{GxSx})$; I_{GySy}=68 mA; V_{SS}=8 V; parameter: T_j

Diagram 11: Typ. transfer gate current characteristics



$I_{GxSx}=f(V_{GxSx})$; I_{GySy}=68 mA; V_{SS}=8 V; parameter: T_j

Diagram 12: Typ. channel reverse characteristics



$I_{SS}=f(V_{SS})$; I_{GySy}=68 mA; T_j=25°C; parameter: V_{GxSx}

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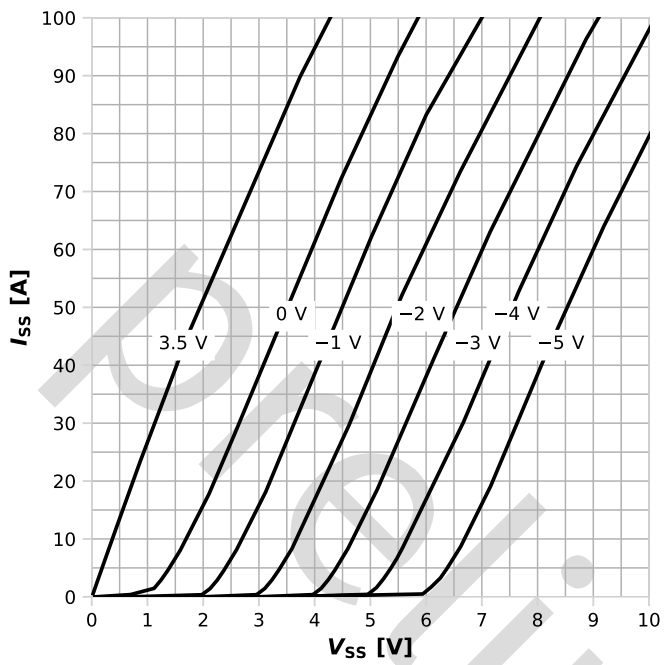
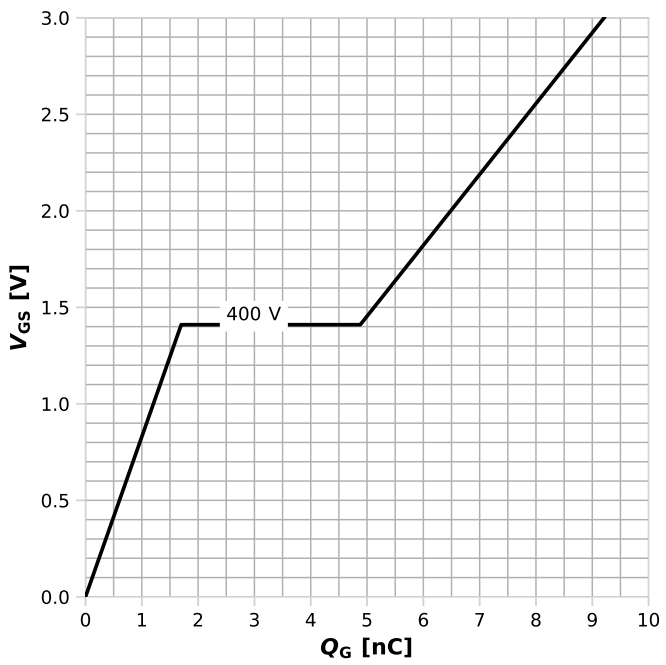
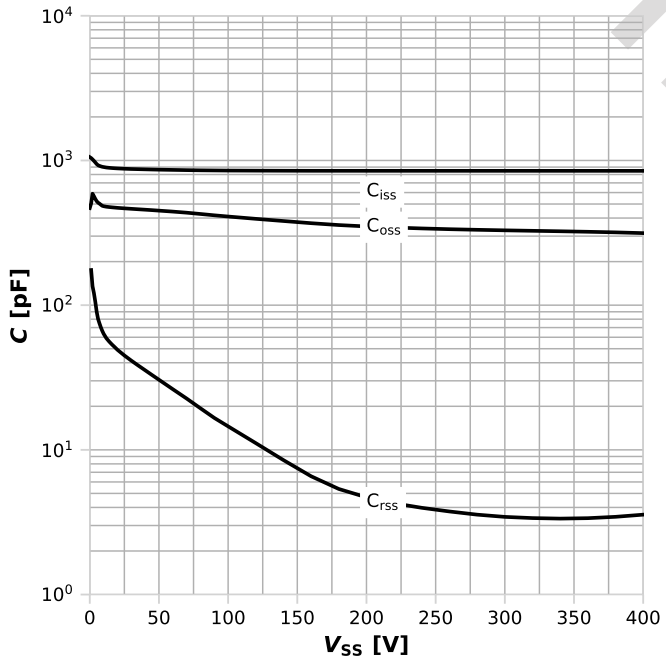
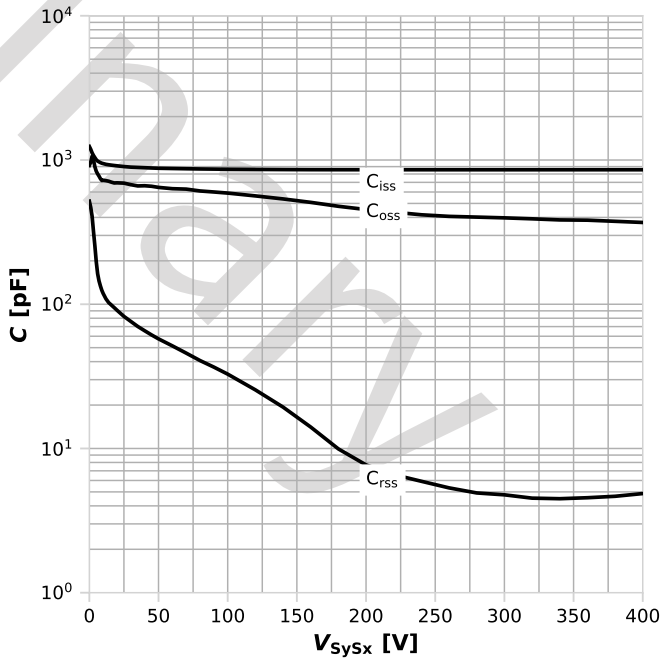
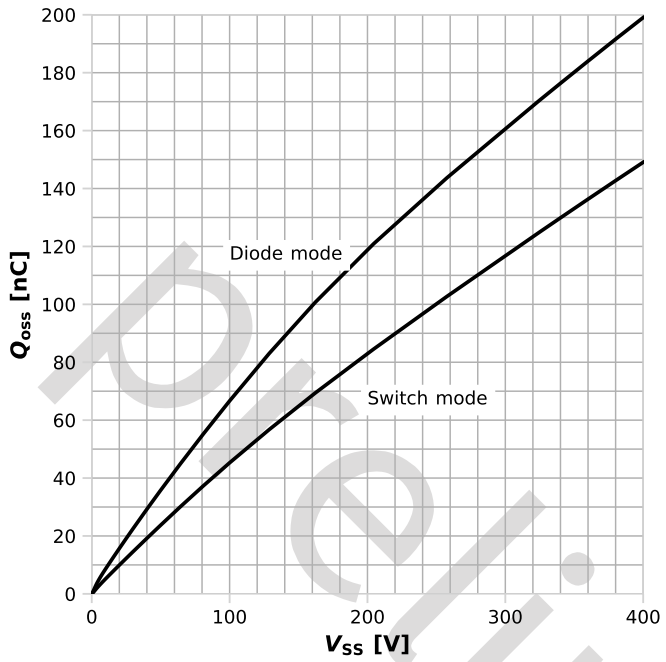
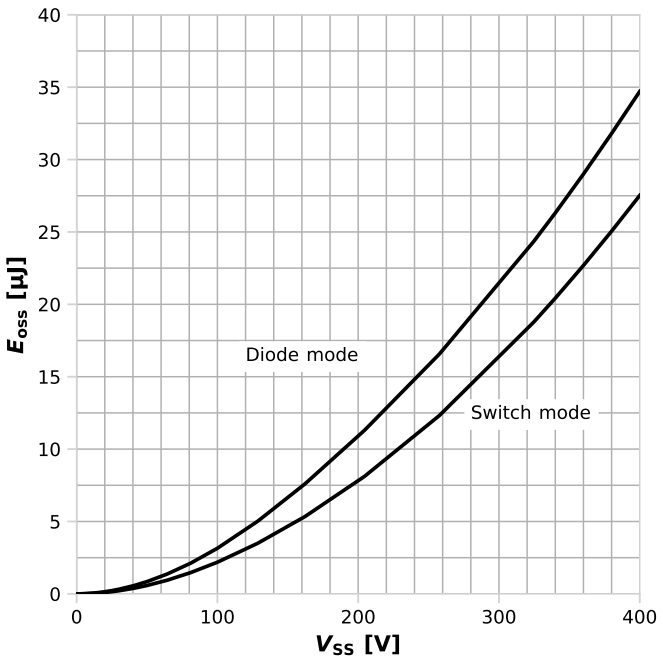
Diagram 13: Typ. channel reverse characteristics	Diagram 14 Typ. gate charge
	
I_{SS}=f(V_{SS}); I_{GySy}=68 mA; T_j=125°C; parameter: V_{GxSx}	V_{GxSx}=f(Q_G); I_{GySy}=68 mA; I_{SS}=20 A pulsed; parameter: V_{SS}

Diagram 15: Typ. capacitances in switch mode (OFF-OFF)	Diagram 16: Typ. capacitances in diode mode (ON-OFF)
	
C_{zss}=f(V_{SS}); V_{GS}=0 V	C_{zss}=f($V_{Sy\text{-}Sx}$); I_{GySy}=0.68 mA; V_{GxSx}=0 V

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Diagram 17: Typ. output charge	Diagram 18: Typ. Coss stored Energy
	
Q_{oss}=f(V_{SS}); parameter: modes	E_{oss}=f(V_{SS}); parameter: modes

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5 Test circuits

Table 8 Gate current switching waveform

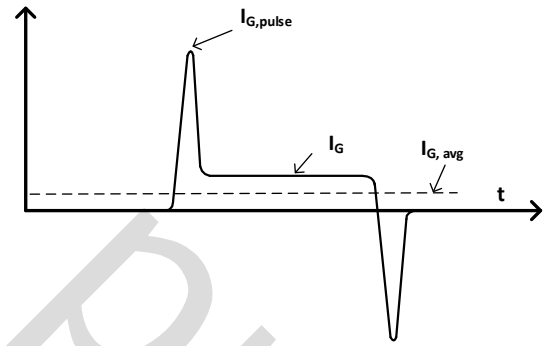
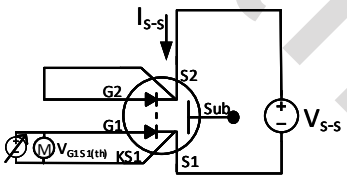
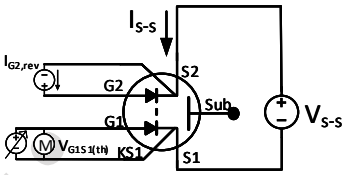
Gate current switching waveform


Table 9 Test condition

$V_{GxSx(th)}$ test condition (diode mode)	$V_{GxSx(th)}$ test condition (switch mode)
	
Switch mode (OFF) → Diode mode	Diode mode → Switch mode (ON)

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6 Modes of operation

Table 10 Switch mode

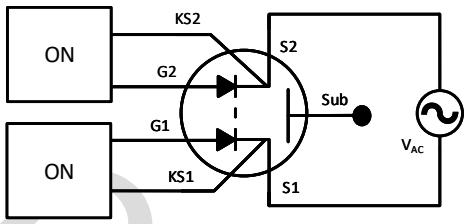
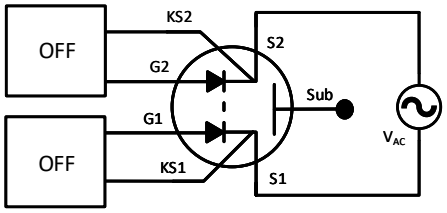
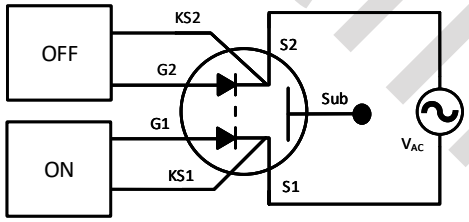
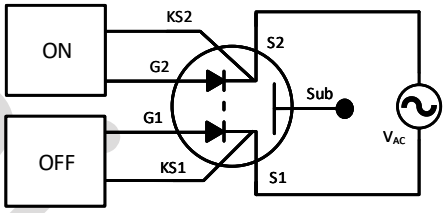
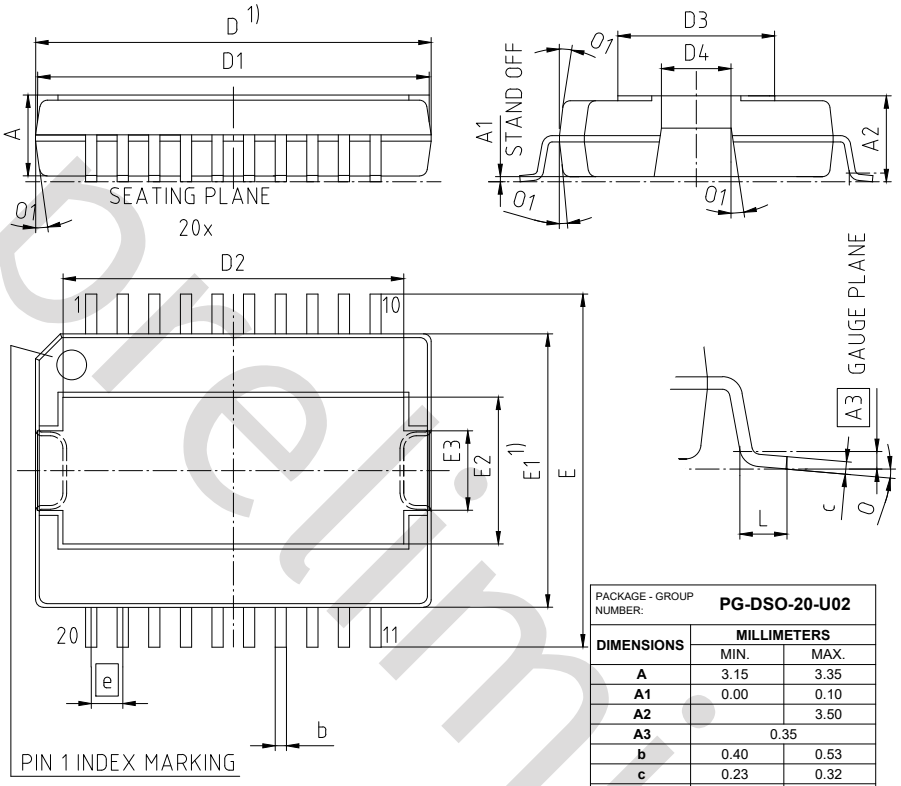
Switch mode (ON-ON)	Switch mode (OFF-OFF)
	

Table 11 Diode mode

Diode mode (OFF-ON)	Diode mode (OFF-ON)
	

Preliminary

7 Package outlines



PACKAGE - GROUP NUMBER:	PG-DSO-20-U02	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	3.15	3.35
A1	0.00	0.10
A2		3.50
A3	0.35	
b	0.40	0.53
c	0.23	0.32
D	15.75	16.50
D1	15.64	15.84
D2	13.50	13.70
D3	6.10	6.50
D4	2.70	2.90
E	13.90	14.50
E1	10.85	11.15
E2	5.80	6.00
E3	3.10	3.30
e	1.27	
L	0.80	1.10
O	2°	8°
O1	8°	

1) DOES NOT INCLUDE PLASTIC OR METAL PRUTRUSION OF 0.15 MAX. PER SIDE

Figure 1 Outline PG-DSO-20, dimensions in mm

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8 Appendix A

Table 12 Related links

- IFX CoolGaN™ GaN 650 V webpage
- IFX CoolGaN™ GaN 650 V reliability white paper
- IFX CoolGaN™ GaN 650 V gate driver application note
- IFX CoolGaN™ GaN 650 V applications information

preliminary

Revision history

IGOT65R025B3

Revision 2026-06-12, Rev. 0.2

Previous revisions

Revision	Date	Subjects (major changes since last revision)
0.1	2026-01-31	Release of preliminary version
0.2	2026-06-12	Preliminary

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Important notice

The product is not developed and released for series supply by Infineon.
Subject to the development and release of the product for series supply by Infineon, the technical specifications of the product are set forth in the relevant final product data sheet provided by Infineon.

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